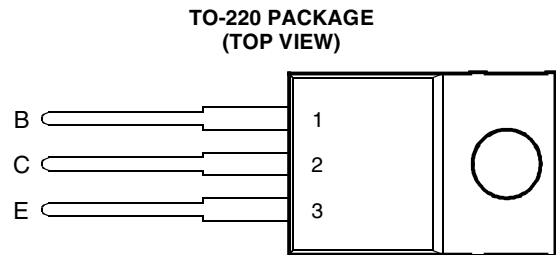


- Designed for Complementary Use with TIP115, TIP116 and TIP117
- 50 W at 25°C Case Temperature
- 4 A Continuous Collector Current
- Minimum h_{FE} of 500 at 4V, 2 A



Pin 2 is in electrical contact with the mounting base.

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absolute maximum ratings at 25°C case temperature (unless otherwise noted)

RATING		SYMBOL	VALUE	UNIT
Collector-base voltage ($I_E = 0$)	TIP110	V_{CBO}	60	V
	TIP111		80	
	TIP112		100	
Collector-emitter voltage ($I_B = 0$)	TIP110	V_{CEO}	60	V
	TIP111		80	
	TIP112		100	
Emitter-base voltage		V_{EBO}	5	V
Continuous collector current		I_C	4	A
Peak collector current (see Note 1)		I_{CM}	6	A
Continuous base current		I_B	50	mA
Continuous device dissipation at (or below) 25°C case temperature (see Note 2)		P_{tot}	50	W
Continuous device dissipation at (or below) 25°C free air temperature (see Note 3)		P_{tot}	2	W
Unclamped inductive load energy (see Note 4)		$\frac{1}{2}LI_C^2$	25	mJ
Operating junction temperature range		T_j	-65 to +150	°C
Storage temperature range		T_{stg}	-65 to +150	°C
Lead temperature 3.2 mm from case for 10 seconds		T_L	260	°C

NOTES: 1. This value applies for $t_p \leq 0.3$ ms, duty cycle $\leq 10\%$.
2. Derate linearly to 150°C case temperature at the rate of 0.4 W/°C.
3. Derate linearly to 150°C free air temperature at the rate of 16 mW/°C.
4. This rating is based on the capability of the transistor to operate safely in a circuit of: $L = 20$ mH, $I_{B(on)} = 5$ mA, $R_{BE} = 100 \Omega$, $V_{BE(off)} = 0$, $R_S = 0.1 \Omega$, $V_{CC} = 20$ V.

PRODUCT INFORMATION

electrical characteristics at 25°C case temperature

PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
$V_{(BR)CEO}$ Collector-emitter breakdown voltage	$I_C = 30 \text{ mA}$ $I_B = 0$ (see Note 5)	TIP110 60 TIP111 80 TIP112 100			V
I_{CEO} Collector-emitter cut-off current	$V_{CE} = 30 \text{ V}$ $V_{CE} = 40 \text{ V}$ $V_{CE} = 50 \text{ V}$ $I_B = 0$ $I_B = 0$ $I_B = 0$			2 2 2	mA
I_{CBO} Collector cut-off current	$V_{CB} = 60 \text{ V}$ $V_{CB} = 80 \text{ V}$ $V_{CB} = 100 \text{ V}$ $I_E = 0$ $I_E = 0$ $I_E = 0$			1 1 1	mA
I_{EBO} Emitter cut-off current	$V_{EB} = 5 \text{ V}$ $I_C = 0$			2	mA
h_{FE} Forward current transfer ratio	$V_{CE} = 4 \text{ V}$ $V_{CE} = 4 \text{ V}$ $I_C = 1 \text{ A}$ $I_C = 2 \text{ A}$	(see Notes 5 and 6) 1000 500			
$V_{CE(sat)}$ Collector-emitter saturation voltage	$I_B = 8 \text{ mA}$ $I_C = 2 \text{ A}$	(see Notes 5 and 6)		2.5	V
V_{BE} Base-emitter voltage	$V_{CE} = 4 \text{ V}$ $I_C = 2 \text{ A}$	(see Notes 5 and 6)		2.8	V
V_{EC} Parallel diode forward voltage	$I_E = 4 \text{ A}$ $I_B = 0$	(see Notes 5 and 6)		3.5	V

NOTES: 5. These parameters must be measured using pulse techniques, $t_p = 300 \mu\text{s}$, duty cycle $\leq 2\%$.
6. These parameters must be measured using voltage-sensing contacts, separate from the current carrying contacts.

resistive-load-switching characteristics at 25°C case temperature

PARAMETER	TEST CONDITIONS [†]	MIN	TYP	MAX	UNIT
t_{on} Turn-on time	$I_C = 2 \text{ A}$ $I_{B(on)} = 8 \text{ mA}$ $I_{B(off)} = -8 \text{ mA}$		2.6		μs
t_{off} Turn-off time	$V_{BE(off)} = -5 \text{ V}$ $R_L = 15 \Omega$ $t_p = 20 \mu\text{s}$, dc $\leq 2\%$		4.5		μs

[†] Voltage and current values shown are nominal; exact values vary slightly with transistor parameters.

TYPICAL CHARACTERISTICS

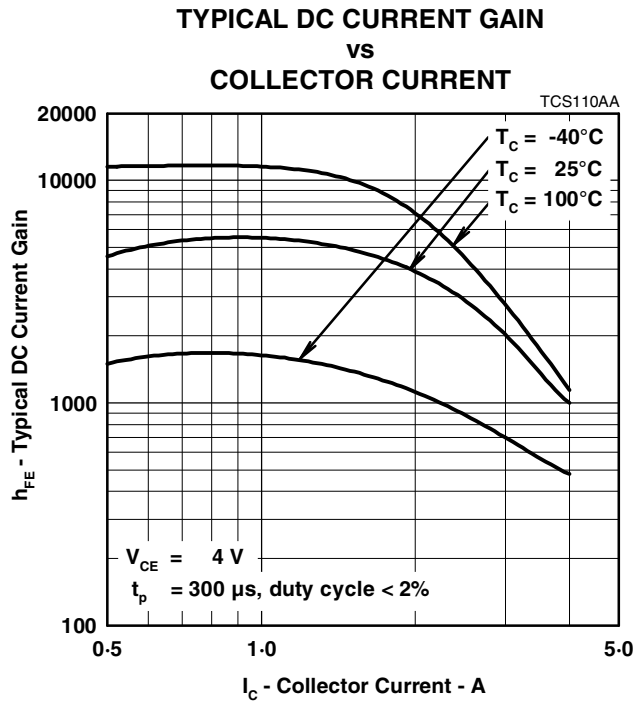


Figure 1.

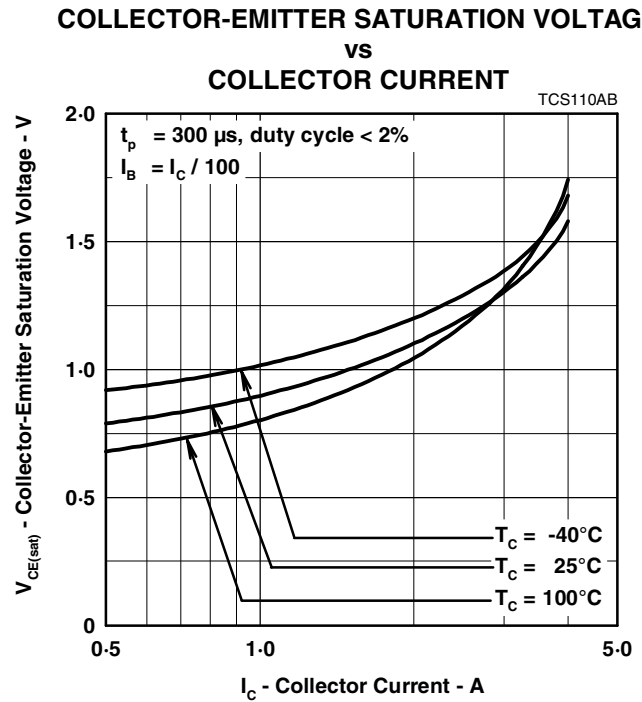


Figure 2.

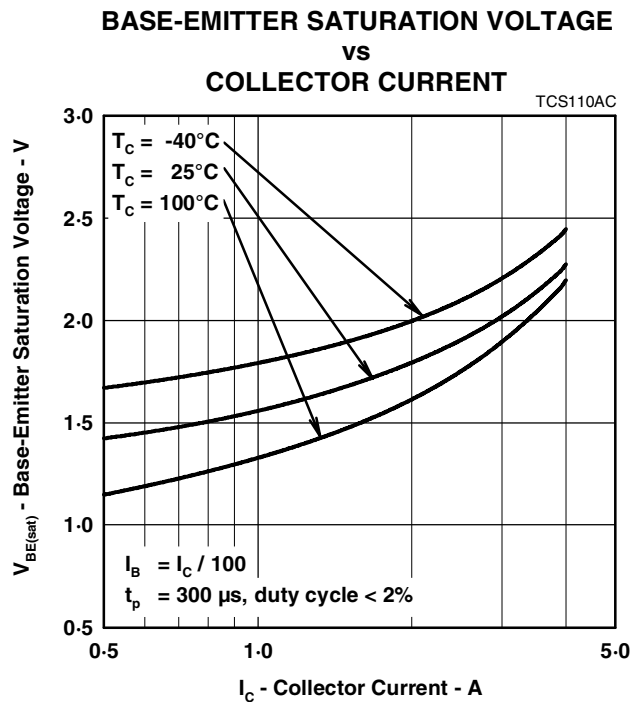


Figure 3.

PRODUCT INFORMATION

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MAXIMUM SAFE OPERATING REGIONS

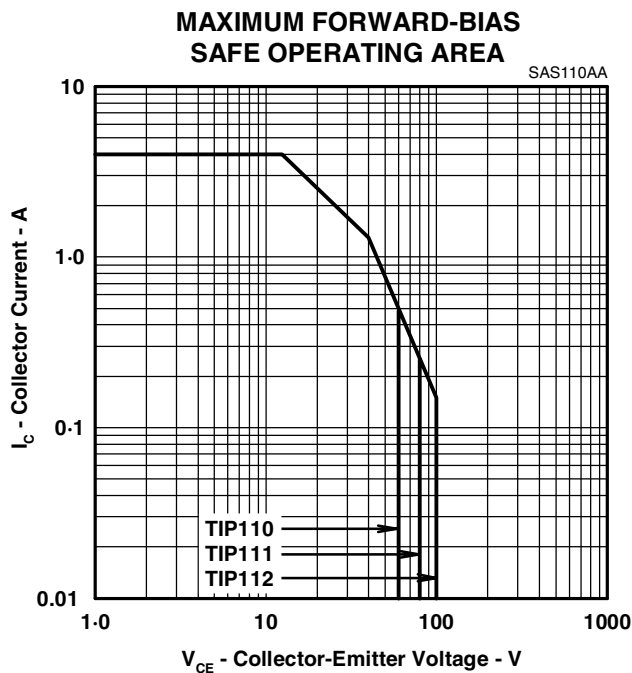


Figure 4.

THERMAL INFORMATION

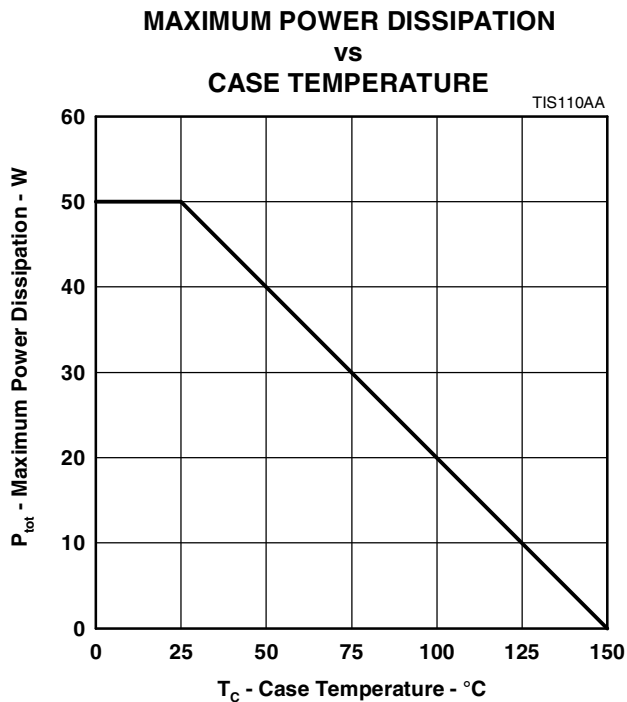


Figure 5.

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